

isc Thyristors

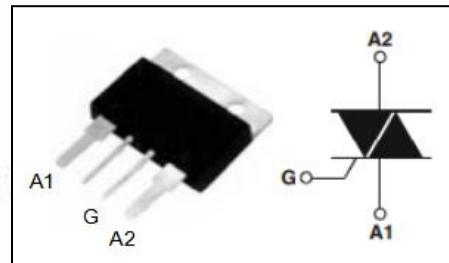
BTA80-800B

DESCRIPTION

- With TO-P4 packaging
- Advanced technology to provide customers with high commutation performances
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Switching applications
- Phase control
- Static switching on inductive or resistive load



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	MAX	UNIT
V_{DRM}	Repetitive peak off-state voltage	800	V
V_{RRM}	Repetitive peak reverse voltage	800	V
$I_{\text{T(RSM)}}$	Average on-state current	80	A
I_{TSM}	Surge non-repetitive on-state current	800	A
T_j	Operating junction temperature	-40~125	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-40~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_R=V_{\text{RRM}}$ $V_D=V_{\text{DRM}}$		1.5	mA
I_{DRM}	Repetitive peak off-state current				
V_{TM}	On-state voltage	$I_T=120\text{A}$		1.5	V
I_{GT}	Gate-trigger current	$V_D=12\text{V}; R_L=10\Omega;$	I	50	mA
			II	50	
			III	50	
			IV	80	
V_{GT}	Gate-trigger voltage	$V_D=12\text{V}; R_L=10\Omega;$		1.3	V
I_{H}	Holding current			80	mA